

ELECTROPOLISHING METAL LAYERS ON WAFERS HAVING TRENCHES OR VIAS WITH DUMMY STRUCTURES

ABSTRACT

A structure is formed on a semiconductor wafer by forming a dielectric layer with a recessed area and a non-recessed area. A plurality of dummy structures are formed within the recessed area, where the dummy structures are inactive areas configured to increase the planarity of a metal layer subsequently formed on the dielectric layer. A metal layer is then formed to fill the recessed area and cover the non-recessed area and the plurality of dummy structures. The metal layer is then electropolished to expose the non-recessed area.